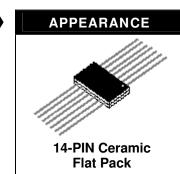


1N5774

Isolated Diode Array with HiRel MQ, MX, MV, and MSP Screening Options

DESCRIPTION

These low capacitance diode arrays are multiple, discrete, isolated junctions fabricated by a planar process and mounted in a 14-PIN package for use as steering diodes protecting up to eight I/O ports from ESD, EFT, or surge by directing them to the positive side of the power supply line and to ground (see figure 1). An external TVS diode may be added between the positive supply line and ground to prevent overvoltage on the supply rail. They may also be used in fast switching core-driver applications. This includes computers and peripheral equipment such as magnetic cores, thin-film memories, plated-wire memories, etc., as well as decoding or encoding applications. These arrays offer many advantages of integrated circuits such as high-density packaging and improved reliability. This is a result of fewer pick and place operations, smaller footprint, smaller weight, and elimination of various discrete packages that may not be as user friendly in PC board mounting.



IMPORTANT: For the most current data, consult MICROSEMI's website: http://www.microsemi.com

FEATURES	APPLICATIONS / BENEFITS
 Hermetic Ceramic Package Isolated Diodes To Eliminate Cross-Talk Voltages High Breakdown Voltage V_{BR} > 60 V at 10 μA Low Leakage I_R< 100nA at 40 V Low Capacitance C < 8.0 pF Options for screening in accordance with MIL-PRF- 19500/474 for JAN, JANTX, JANTXV, and JANS are available by adding MQ, MX, MV, or MSP prefixes respectively to part numbers. For example, designate MX1N5774 for a JANTX screen. 	 High Frequency Data Lines RS-232 & RS-422 Interface Networks Ethernet: 10 Base T Computer I/O Ports LAN Switching Core Drivers IEC 61000-4 Compatible (see circuit in figure 1) 61000-4-2 ESD: Air 15 kV, contact 8 kW 61000-4-4 (EFT): 40 A – 5/50 ns 61000-4-5 (surge): 12 A 8/20 µs
MAXIMUM RATINGS	MECHANICAL AND PACKAGING
 Reverse Breakdown Voltage of 60 Vdc (Note 1 & 2) Continuous Forward Current of 300 mA dc (Note 1 & 3) Peak Surge Current (tp=1/120 s) of 500 mA dc (Note 1) 400 mW Power Dissipation per Junction @ 25°C 500 mW Power Dissipation per Package @ 25°C (Note 4) Operating Junction Temperature range -65 to +150°C Storage Temperature range of -65 to +200°C NOTE 1: Each Diodo 	 14-PIN Ceramic Flat Pack Weight 0.29 grams (approximate) Marking: Logo, part number, date code and dot identifying pin #1 Carrier Tubes; 19 pcs (standard)

NOTE 1: Each Diode

- NOTE 2: Pulsed: Pw = 100 ms max.; duty cycle <20%
- **NOTE 3:** Derate at 2.4 mA/°C above +25°C
- NOTE 4: Derate at 4.0 mW/°C above +25°C

ELECTRICAL CHARACTERISTICS (Per Diode) @25°C unless otherwise specified ΜΔΧΙΜΙΙΜ

	MAXIMUM FORWARD VOLTAGE V _{F1} I _F = 100 mA	MAXIMUM FORWARD VOLTAGE V _{F2} I _F = 500 mA	MAXIMUM REVERSE CURRENT I _{R1}	MAXIMUM CAPACITANCE (PIN TO PIN) C _t V _R = 0 V	MAXIMUM FORWARD RECOVERY TIME t _{fr}	REVERSE RECOVERY TIME trr $I_F = I_R = 200 \text{ mA}$ $i_{rr} = 20 \text{ mA}$	
PART	(Note 1)	(Note 1)	$V_{\rm R} = 40 \text{ V}$	F = 1 MHz	I _F = 500 mA	R _L = 100 ohms	
NUMBER	Vdc	Vdc	μAdc	pF	ns	ns	
1N5774	1	1.5	0.1	8.0	40	20	

NOTE 1: Pulsed: $P_W = 300 \ \mu s \ +/-50 \ \mu s$, duty cycle $\leq 2\%$, 90 μs after leading edge.



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Symbol		DEFINITIO	N						
V_{BR}	Minimum Breakdown Voltage: T								
V_{F}	Maximum Forward Voltage: The maximum forward voltage the device will exhibit at a specified cu								
I _R	Maximum Leakage Current: The maximum leakage current that will flow at the specified voltag temperature.								
Ct	Capacitance: The capacitance o picofarads.	f the TVS as define	ed @ 0 vo	olts at a f	requenc	y of 1 M	Hz and st		
S	CHEMATIC PACKAGE DIMENSIONS								
		$\begin{array}{c} 1 \\ 1 \\ 2 \\ 13 \\ 3 \\ 12 \\ 4 \\ 11 \\ 5 \\ 10 \\ 6 \\ 9 \\ 7 \\ 8 \end{array}$							
Supply	CIRCUIT rail (+V _{CC})								
]	Symbol		hes		meters		
			DI	Min	Max	Min	Max		
		-	BL BW	.235	.390 .260	5.97	9.91 6.60		
I/O Port —	+	-	CH	.235	.200	1.14	2.41		
			LL	.250	.370	6.35	9.40		
	\mathbf{T}	ļ	LO	.005		0.13			
			LO ₂	.026	.045	0.66	1.14		
GNI	$O(\text{or} - V_{CC})$		LS		BSC		BSC		
0.01		-	LT LU	.003	.006 .280	0.08	0.15 7.11		
Steering D	iode Application	-	LU	.010	.280	0.25	0.48		
	IURE 1	L		<u> </u>		+	-		

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